




ISTITUTO ITALIANO DI TECNOLOGIA
CENTER FOR NANO SCIENCE AND TECHNOLOGY

Solution processable photovoltaics: Science and technology

 The Jacob Blaustein Center for Scientific Cooperation
The Jacob Blaustein Institutes for Desert Research
Ben-Gurion University of the Negev

 IKI
Ilse Katz Institute for
Nanoscale Science and Technology

20th Sede Boqer Symposium
on Solar Electricity Production
jointly with the
IKI Annual Nano-Day
and the
BGU-ENEA WORKSHOP
September 26-28, 2016

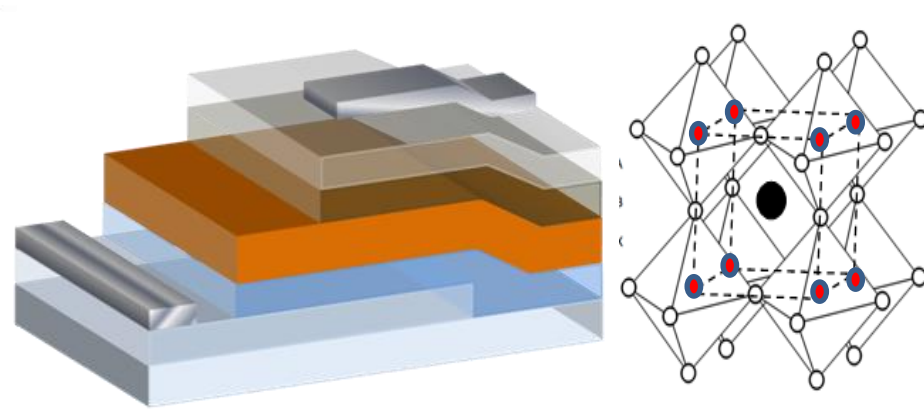
 ENEA
Italian National Agency for New Technologies,
Energy and Sustainable Economic Development

 Ministry of National Infrastructure,
Energy and Water Resources
www.energy.gov.it

Via the Italian Ministry of Foreign Affairs and
International Cooperation (MAECI)

Guglielmo Lanzani

CNST@POLIMI Istituto Italiano di Tecnologia, Milan Italy



Perovskite



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DI TECNOLOGIA

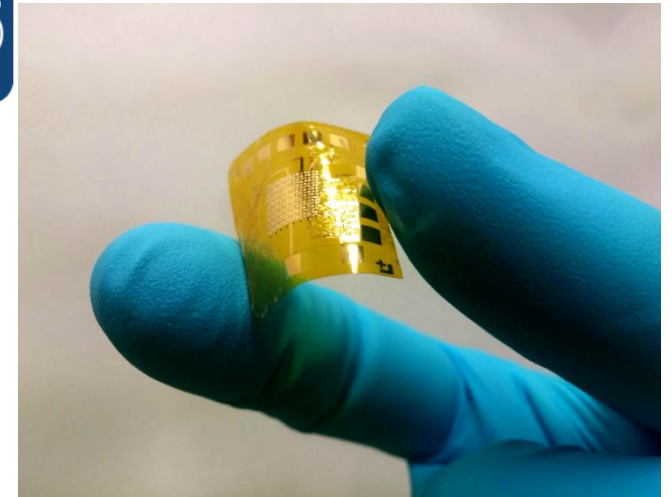
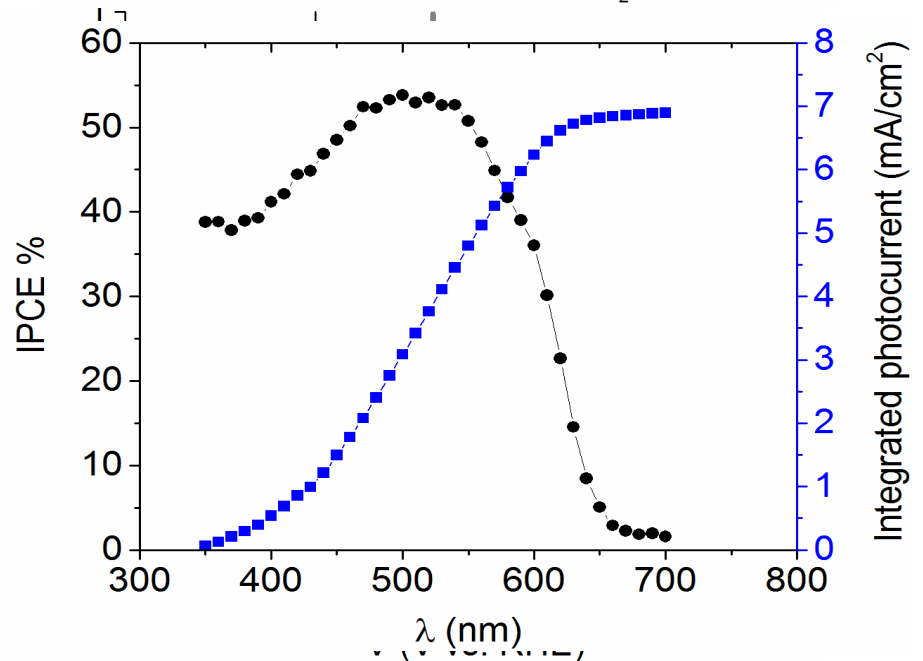
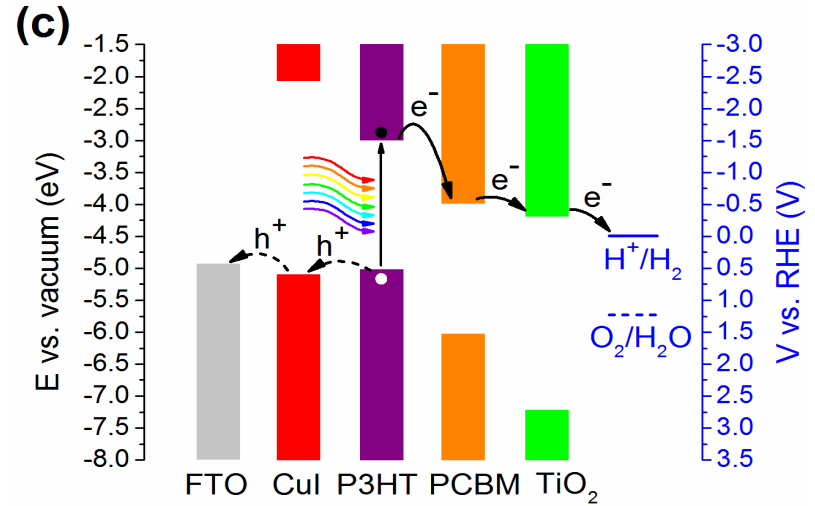
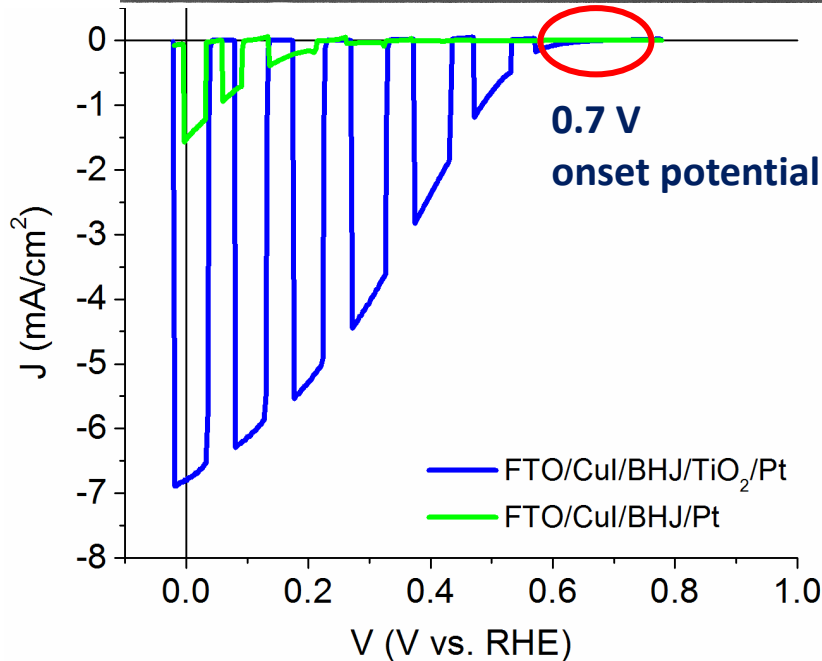
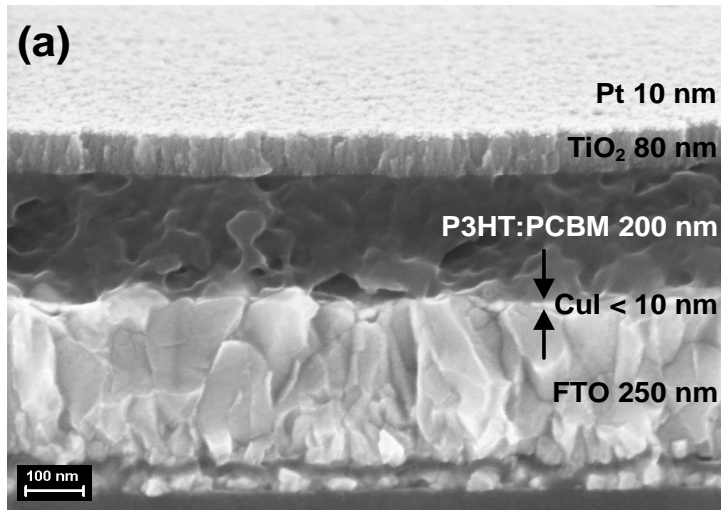


Photo-catalytic Water Splitting

Organic thermoelectricity

Hybrid Organic Photoelectrochemical Water Splitting

Fumagalli et al. JMCA (2016), Comas et al. EES (2016)





ribes
TECHNOLOGIES

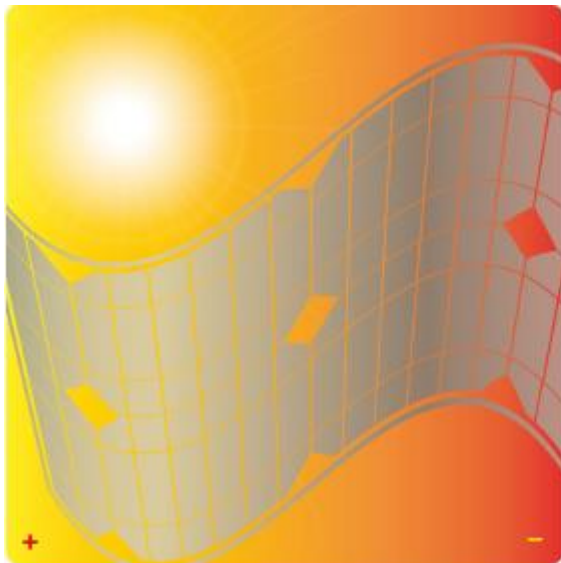
Ribes Technologies will produce plastic photovoltaic (PV) foils



Wireless **power supply** for the internet of things

Global Agenda

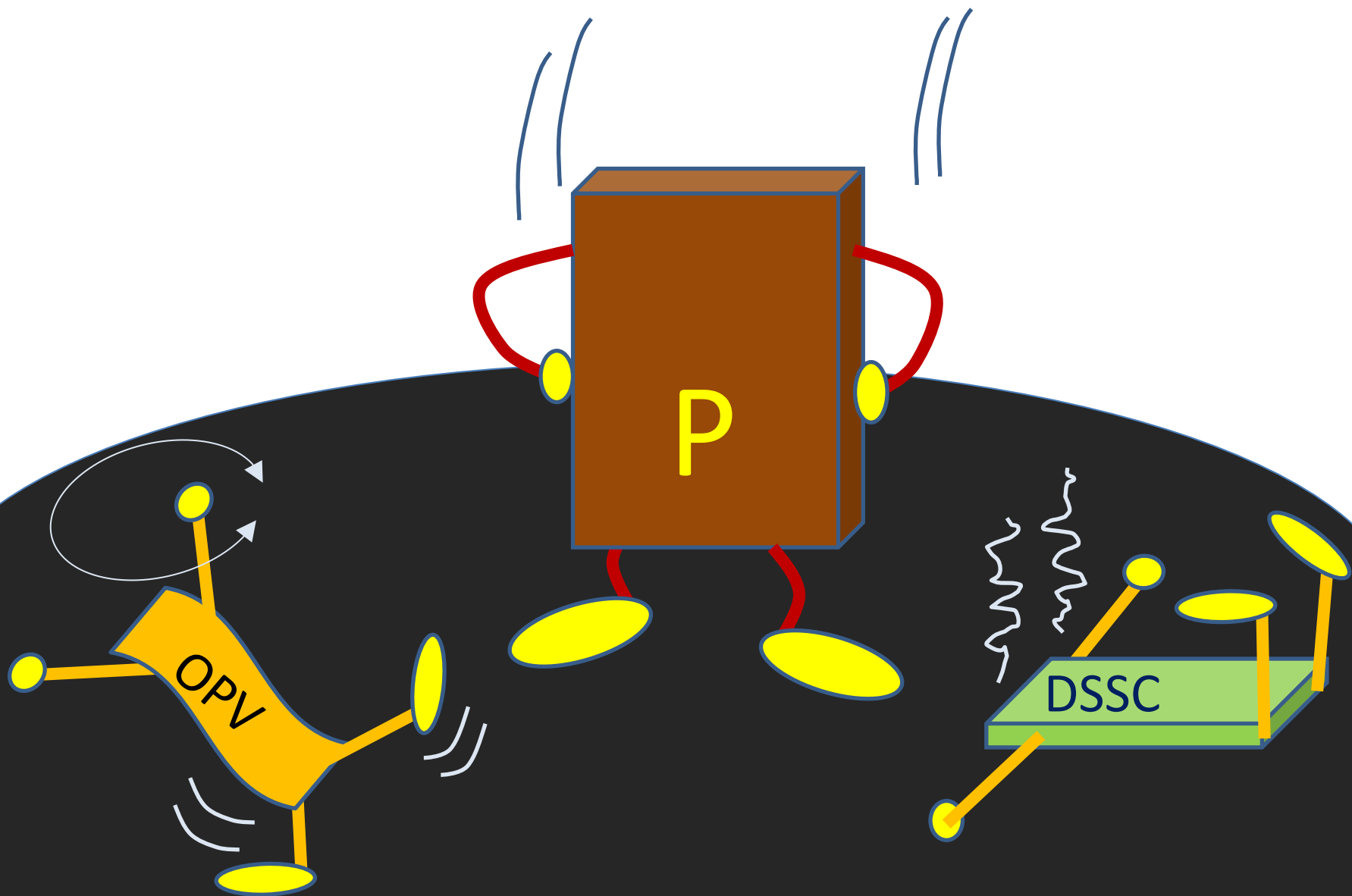
Top 10 Emerging Technologies of 2016

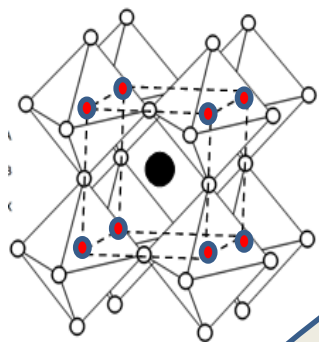


Perovskite Solar Cells

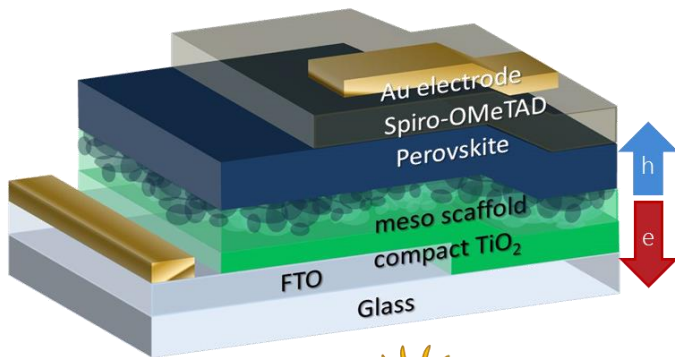
*Making progress towards
ubiquitous solar power generation*

The Perovskite Revolution

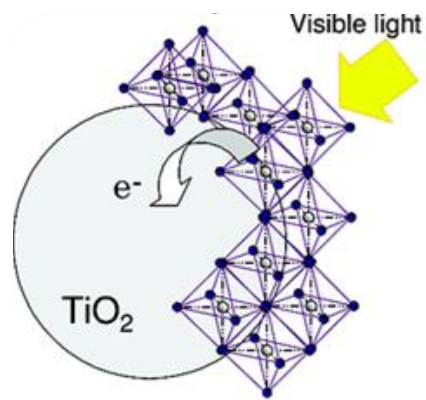




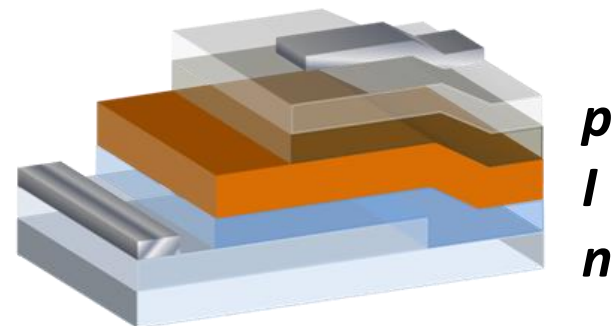
$\eta > 20\%$ (KRICT, EPFL)



Meso-structured



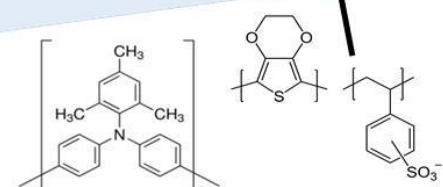
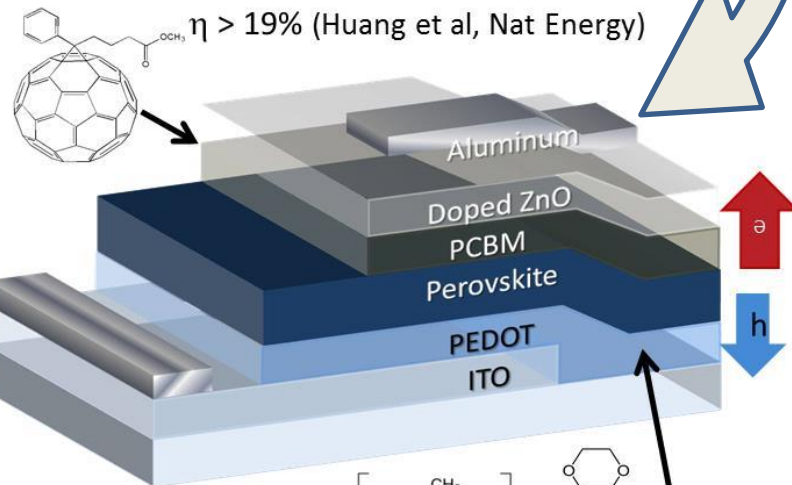
Perovskite nanocrystalline sensitizers



**p
i
n**



$\eta > 19\%$ (Huang et al, Nat Energy)



Planar Solar Cells For Tandem Structure

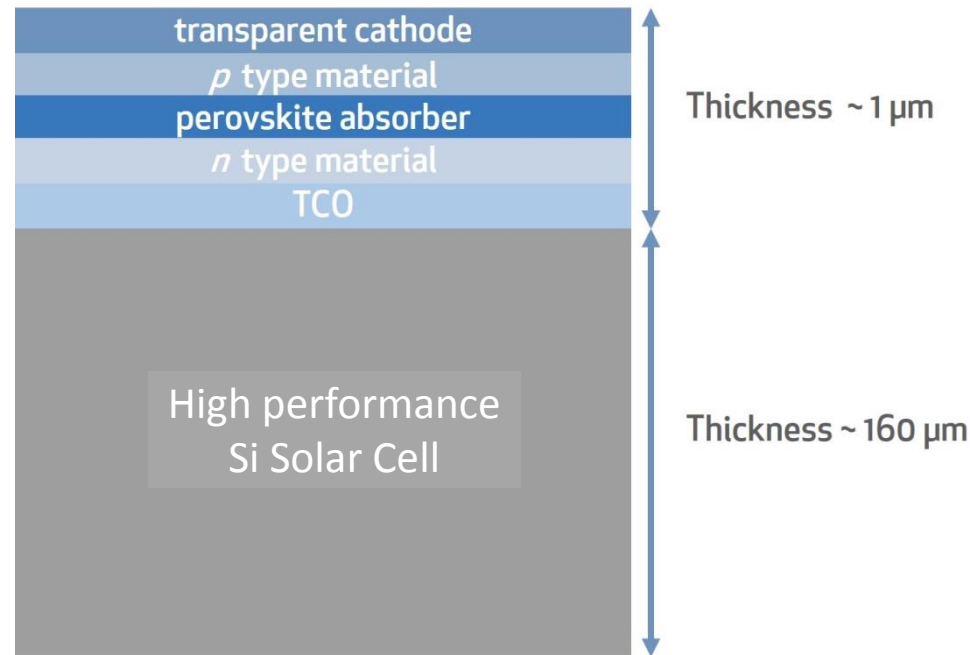
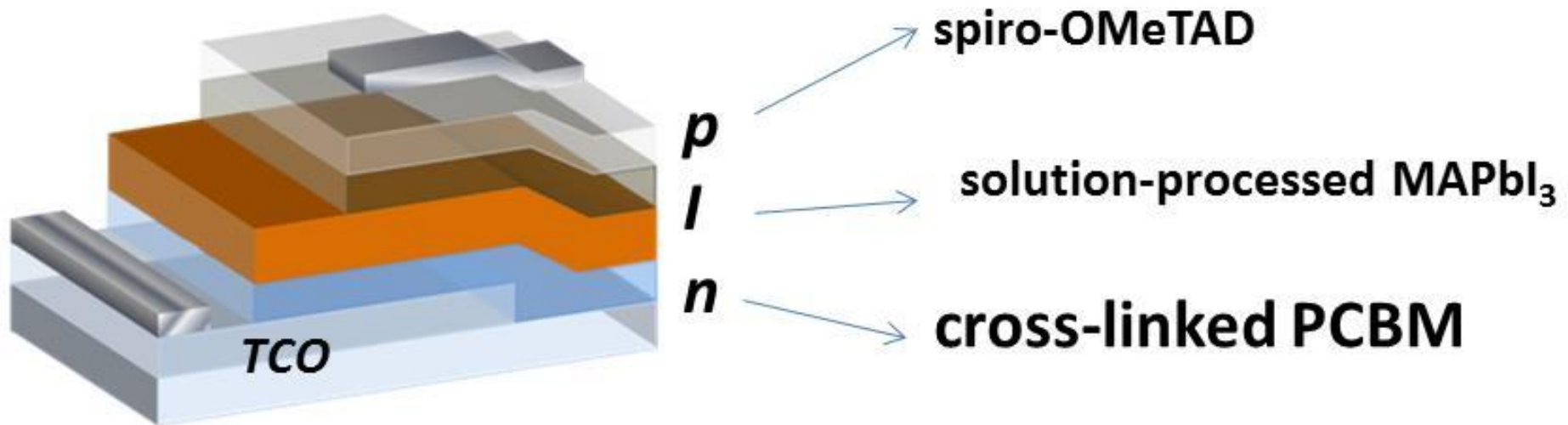


Figure credit: OxfordPV Ltd website

- ✓ Low temperature processing
- ✓ High Efficiency in Steady State Conditions
- ✓ Multi-layers processing

All-Solution Low T Planar Solar Cells

Chen Tao (陶 晨)

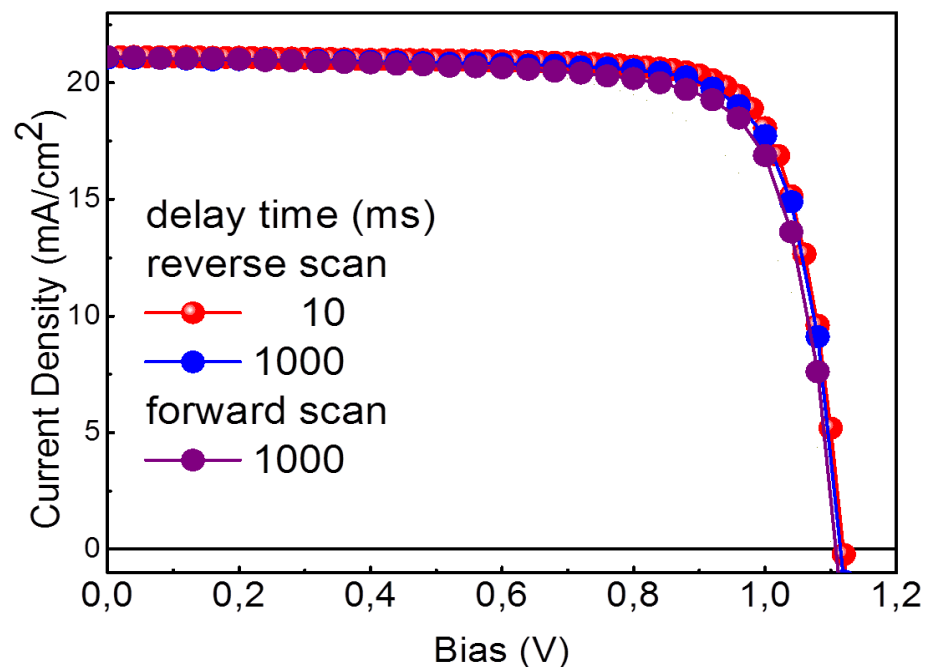
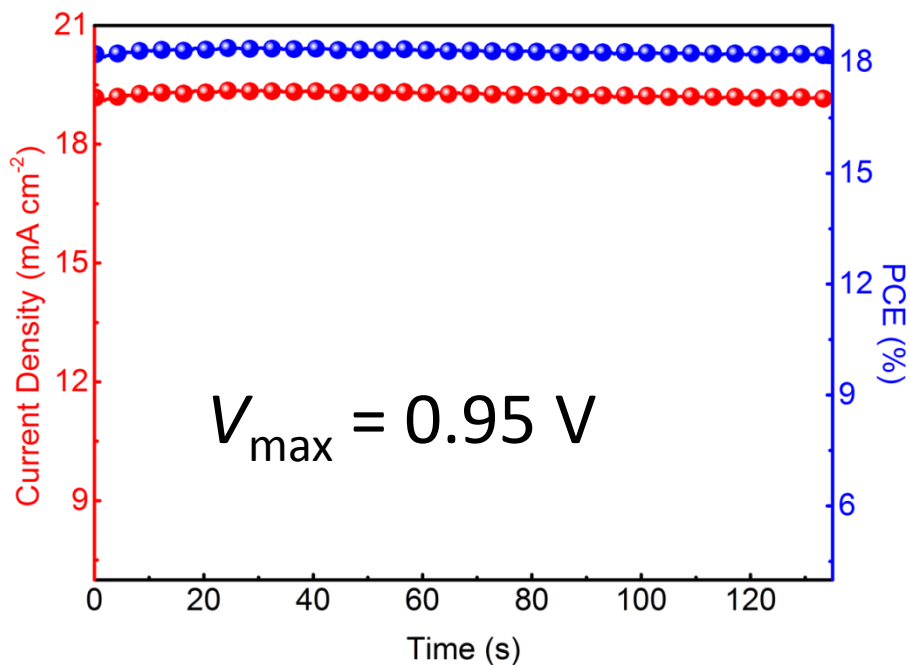


Direct Architecture

C. Tao et al, *submitted*.

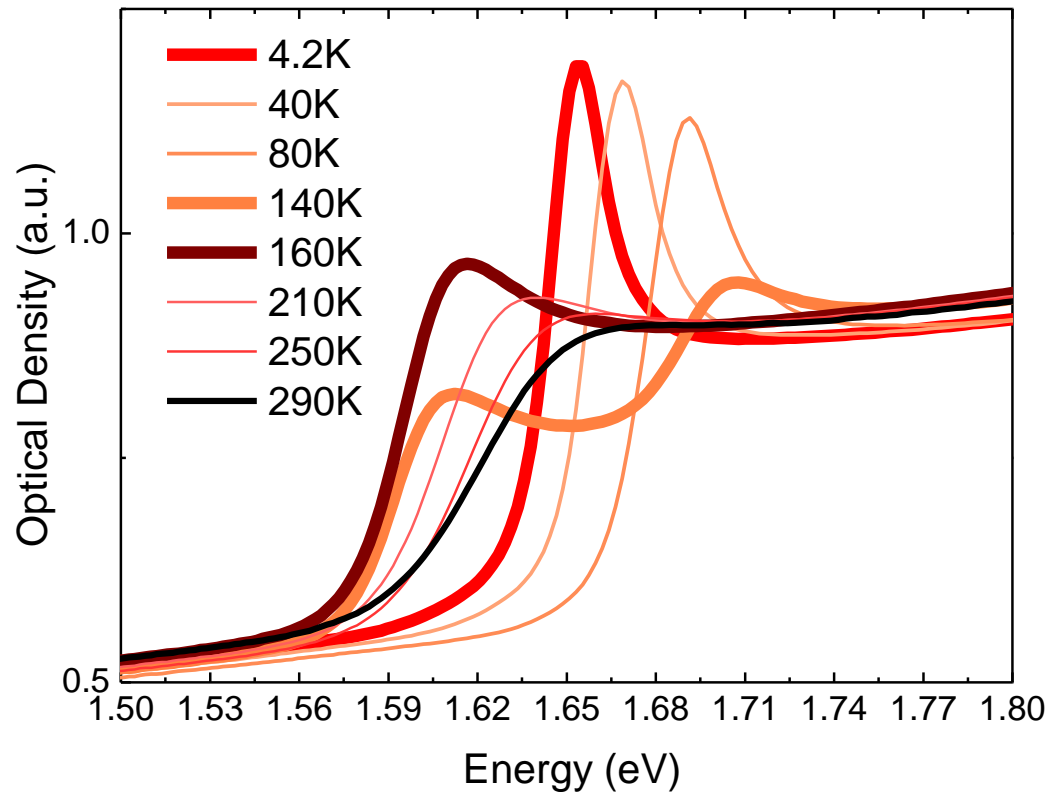
Device performance

TiO₂/x-PCBM



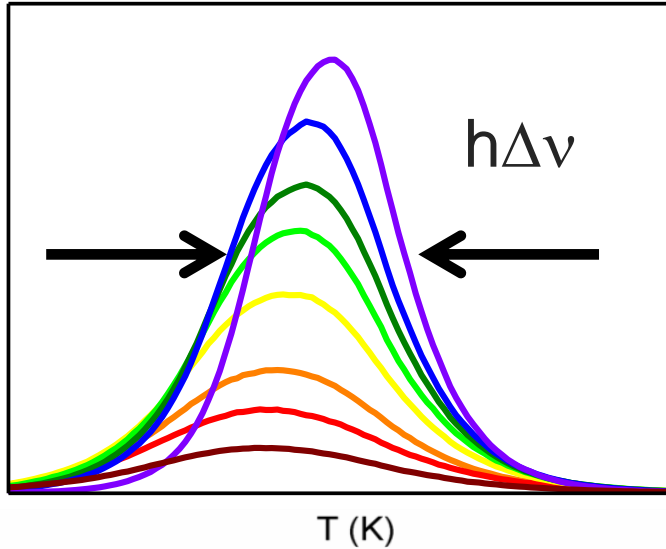
V_{oc} (V)	J_{sc} (mA cm ⁻²)	FF (%)	PCE (%)
1.12	21.1	79	18.7

Which Photoexcitation in working devices?



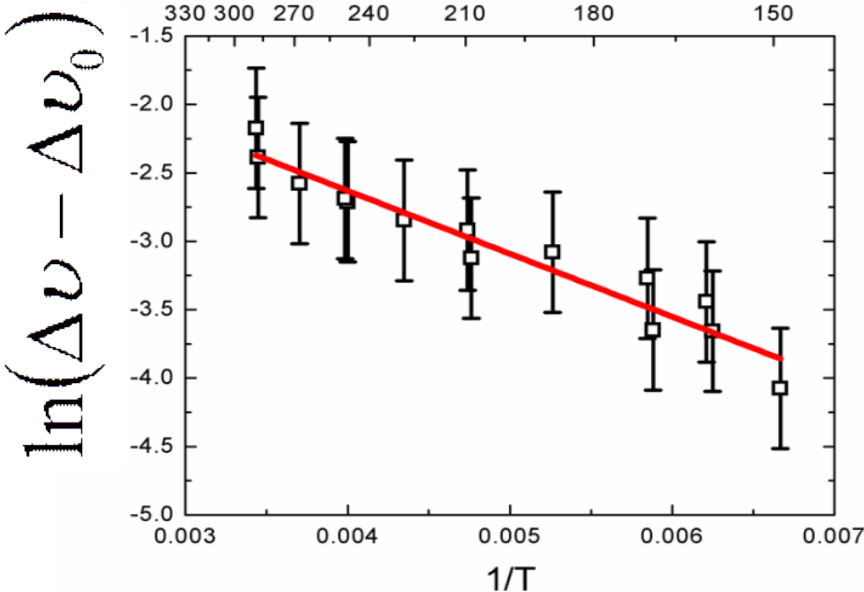
$\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$ on glass substrate

Exciton Binding Energy in $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$



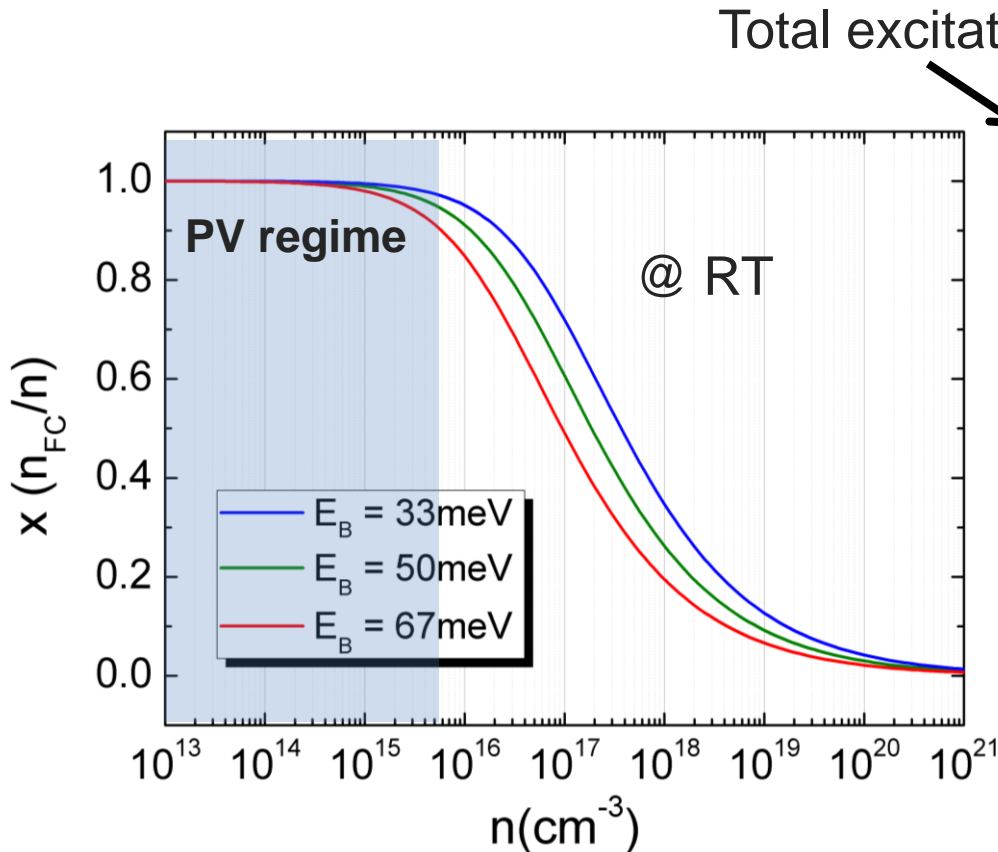
Exciton Binding Energy

$$\Delta\nu = \Delta\nu_0 + \nu_T \exp\left(-\frac{E_b}{k_B T}\right)$$



$E_b = (50 \pm 20) \text{meV}$

Exciton Vs Free Charges at the Thermodynamic Equilibrium

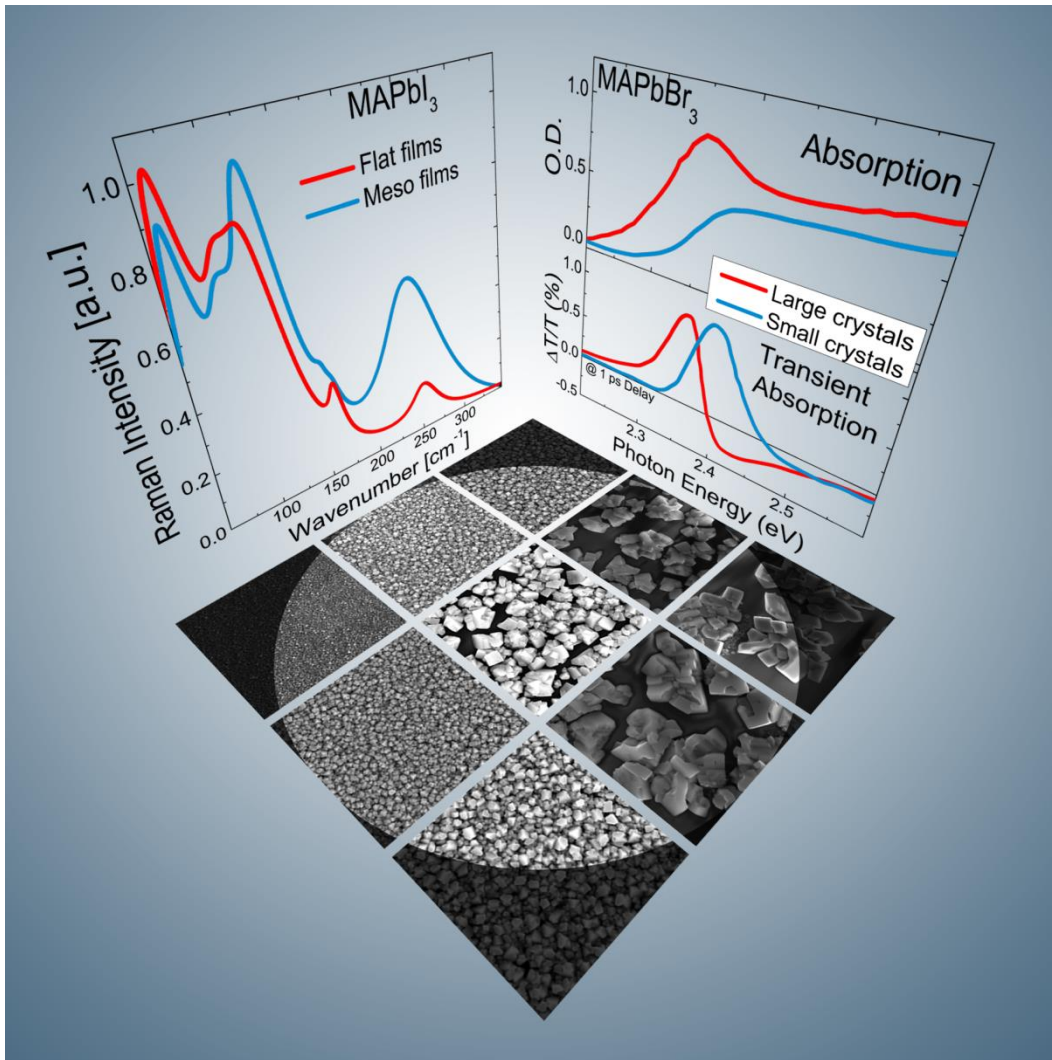


$$n = n_{FC} + n_{exc}$$

$$\frac{n_{FC}}{n_{exc}} = \left(\frac{2\pi\mu k_B T}{h^2} \right)^{3/2} e^{-\frac{E_b}{k_B T}}$$

$$x = \frac{n_{FC}}{n}$$

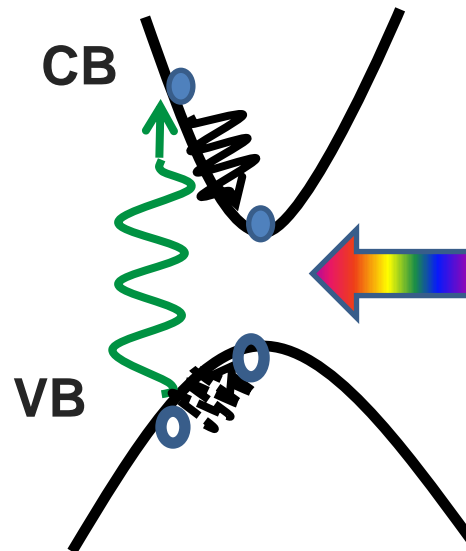
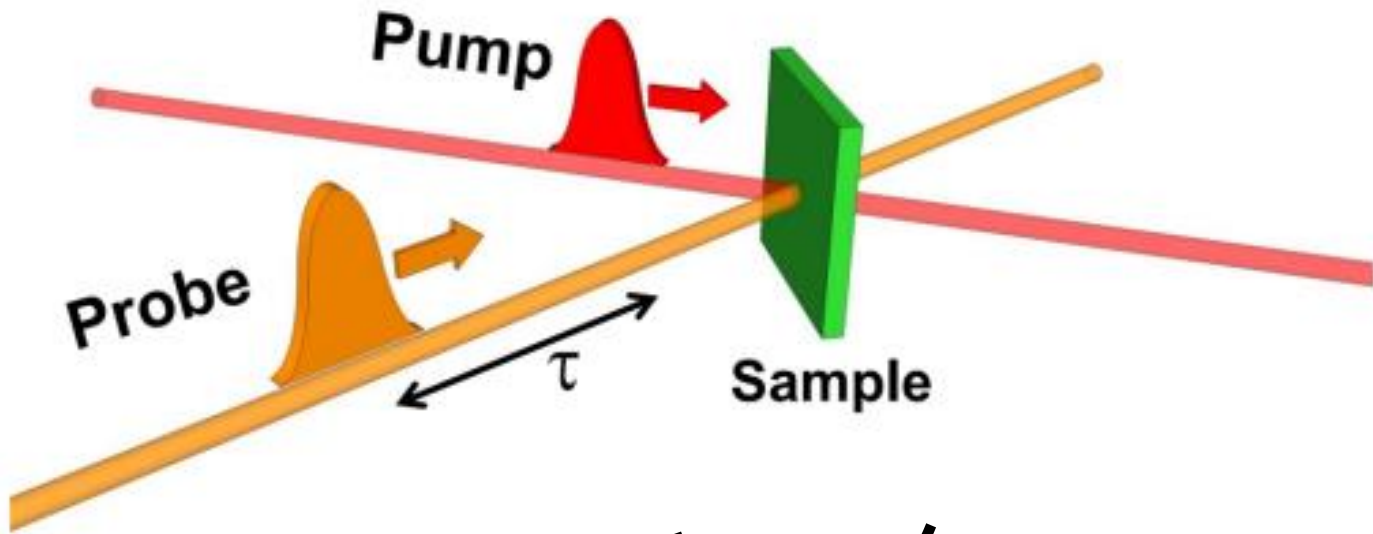
Courtesy: Stefanie Neutzner



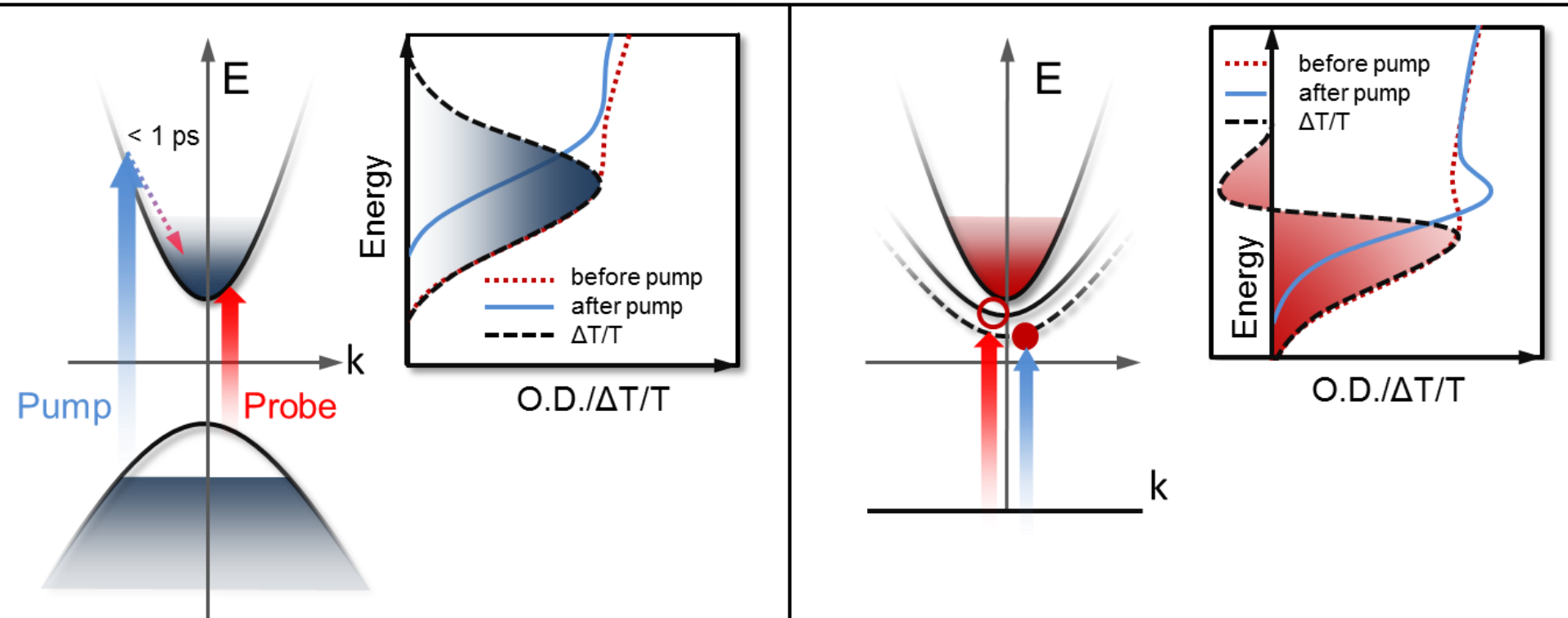
- Excitonic effects and Microstructure
- Related to order/disorder in the material
- Modulation of the dielectric constant?

Grancini, Kandada et al, Nature Photonics 9 (10), 695-701 (2015)
 Kandada and Petrozza, Acc. Chem. Res (2016)

Role of Microstructure in the Electron-Hole Interaction of Hybrid Lead-Halide Perovskites



Intepretation of the transient spectra

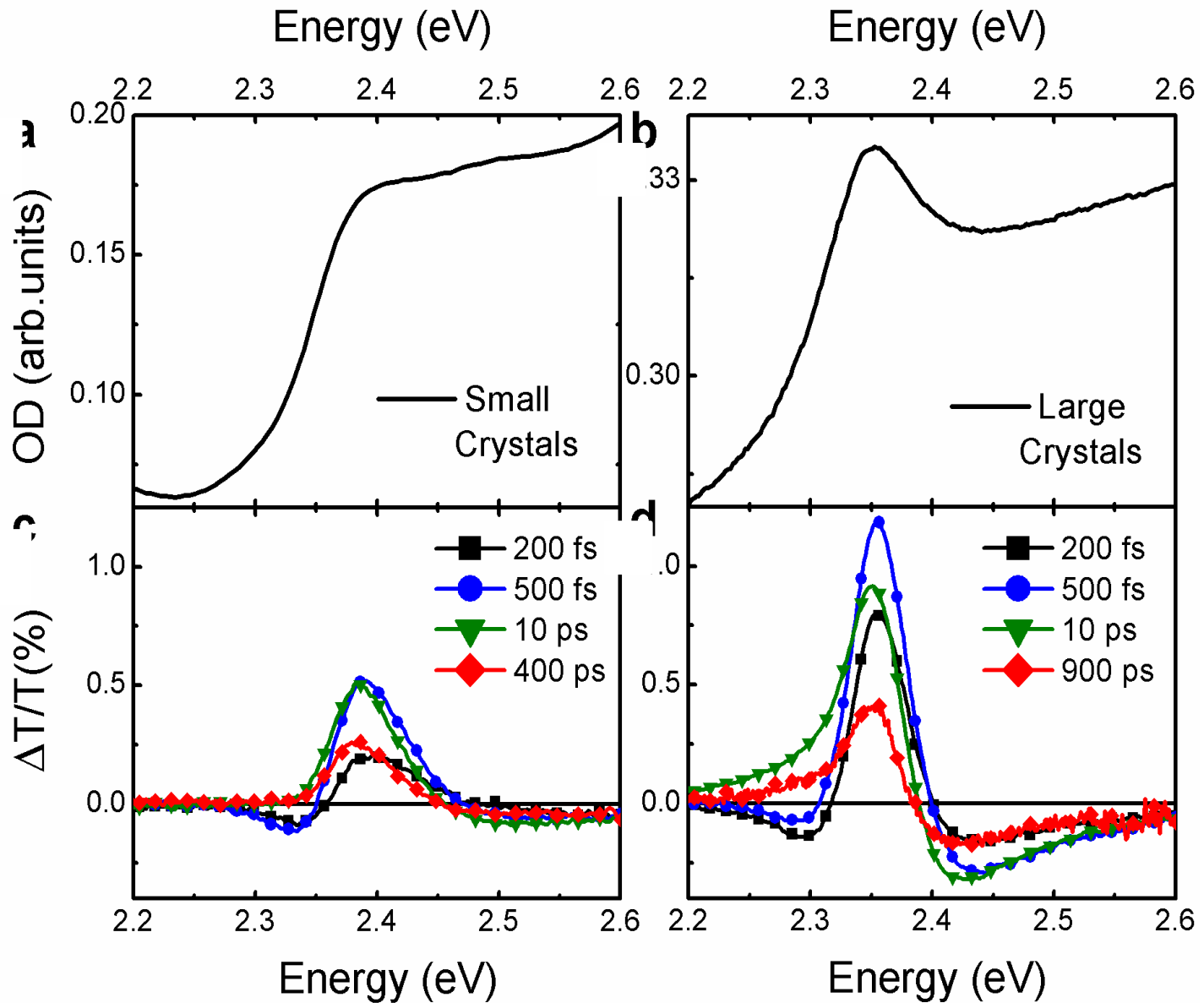


FREE CARRIERS

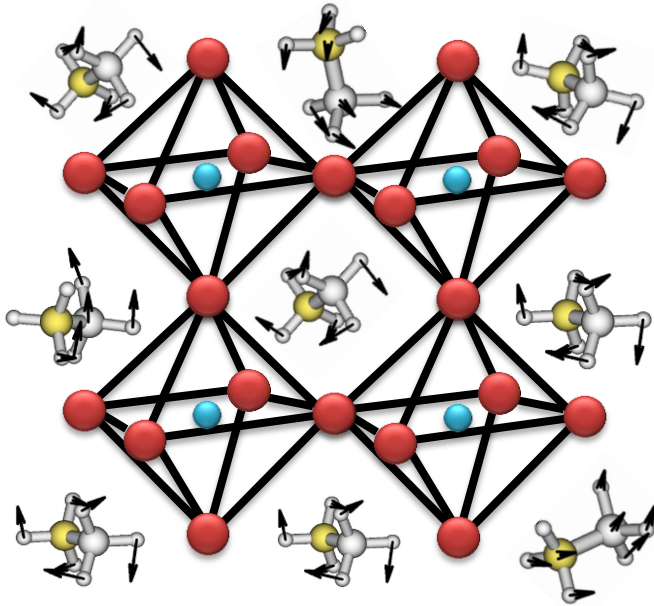
VS

EXCITON

Stable Exciton (RT) MAPbBr₃

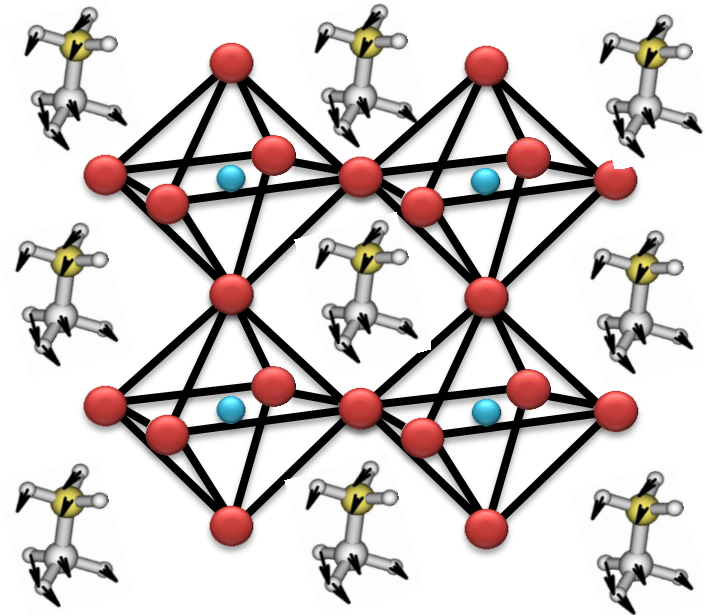


Screening in Perovskites



Free Dipoles

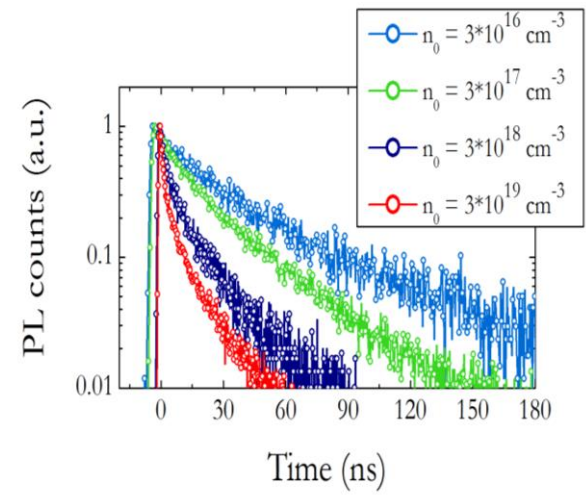
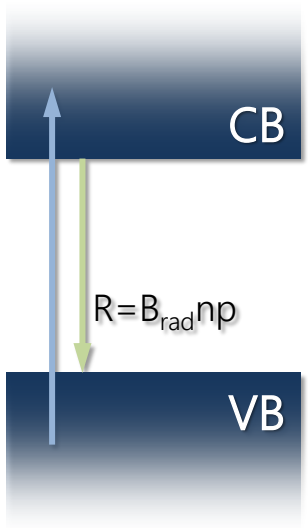
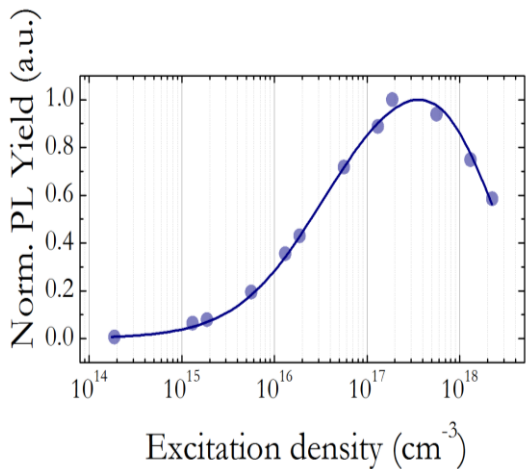
Langevin model: $\epsilon_r \approx 8$



Dipoles twinning

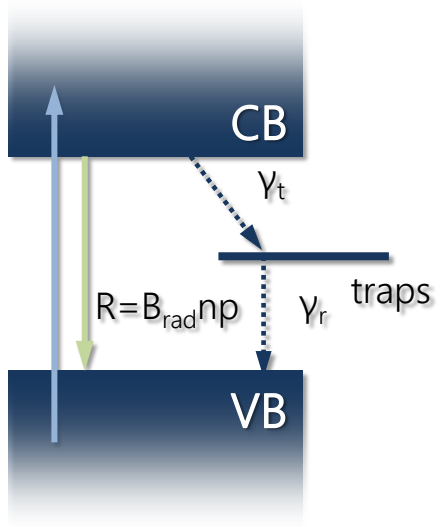
Ferroelectric order

PL in Perovskites

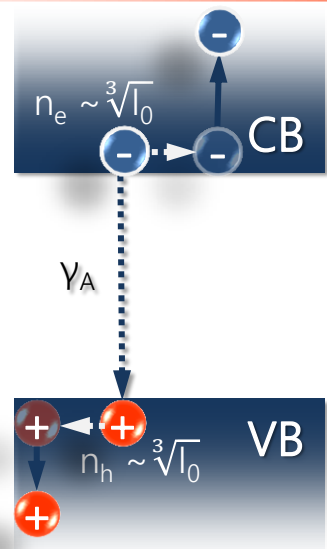


EXCITATION DENSITY

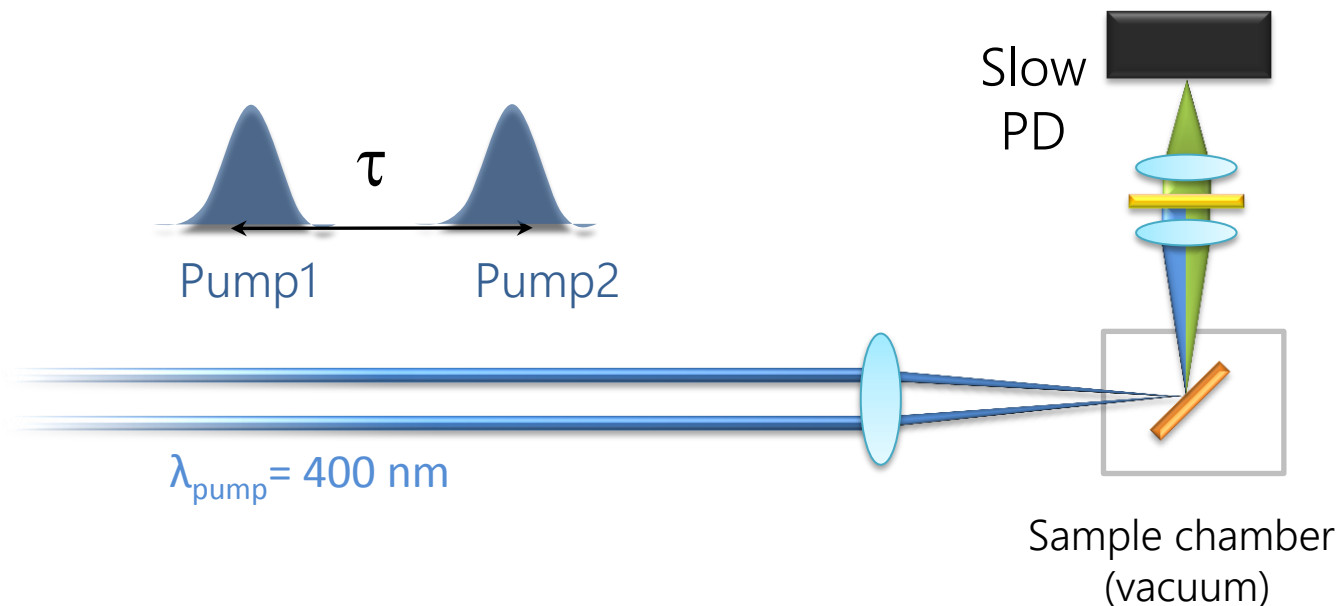
PV regime



Lasing



ECPL : Experimental Principle



Total intensity at photo detector:

$$I(I_0, \tau) = \int_0^{\infty} PL_1(I_0, t) dt + \int_{\tau}^{\infty} PL_2(I_0, t - \tau) dt + \int_{\tau}^{\infty} PL_{\text{cross}}(2I_0, t, t - \tau) dt$$

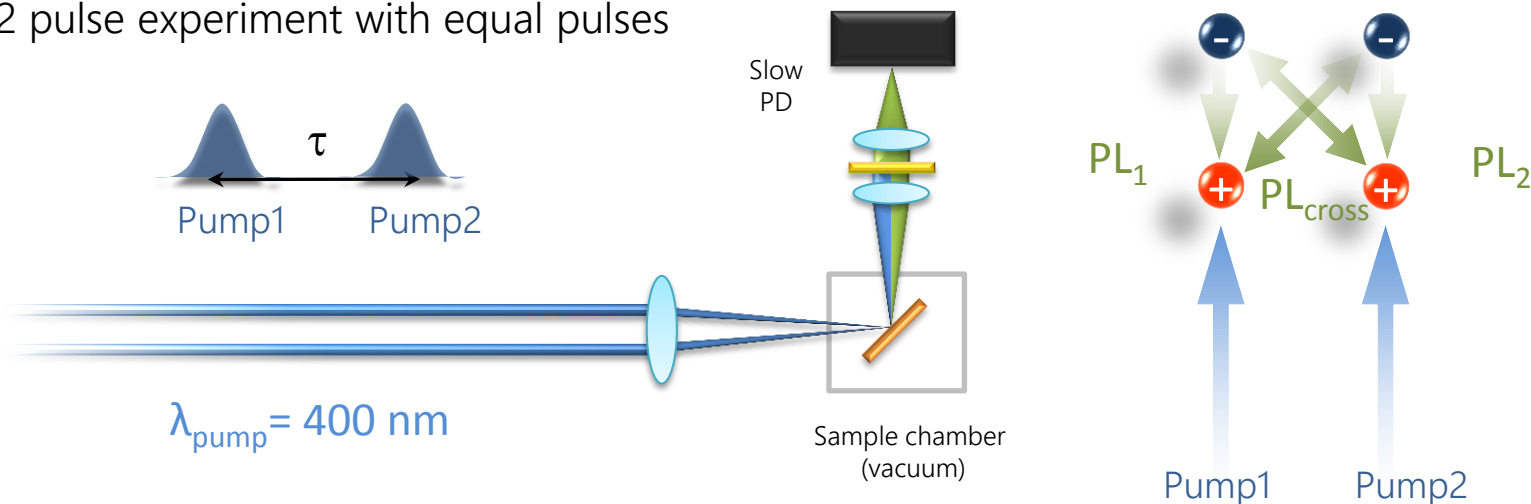
Von der Linde et al, J. Lumin, 24, 675 (1981).

Rosen, Appl. Phys. Lett, 39, 935 (1981).

Borgwardt et al, J. Appl. Phys. 117, 215702(2015)

ECPL : Experimental Principle

2 pulse experiment with equal pulses



Total intensity at photo detector:

$$ECPL (\tau = 0, I) = \frac{PL(2I) - 2PL(I)}{PL(2I)}$$

Von der Linde et al, J. Lumin, 24, 675 (1981).

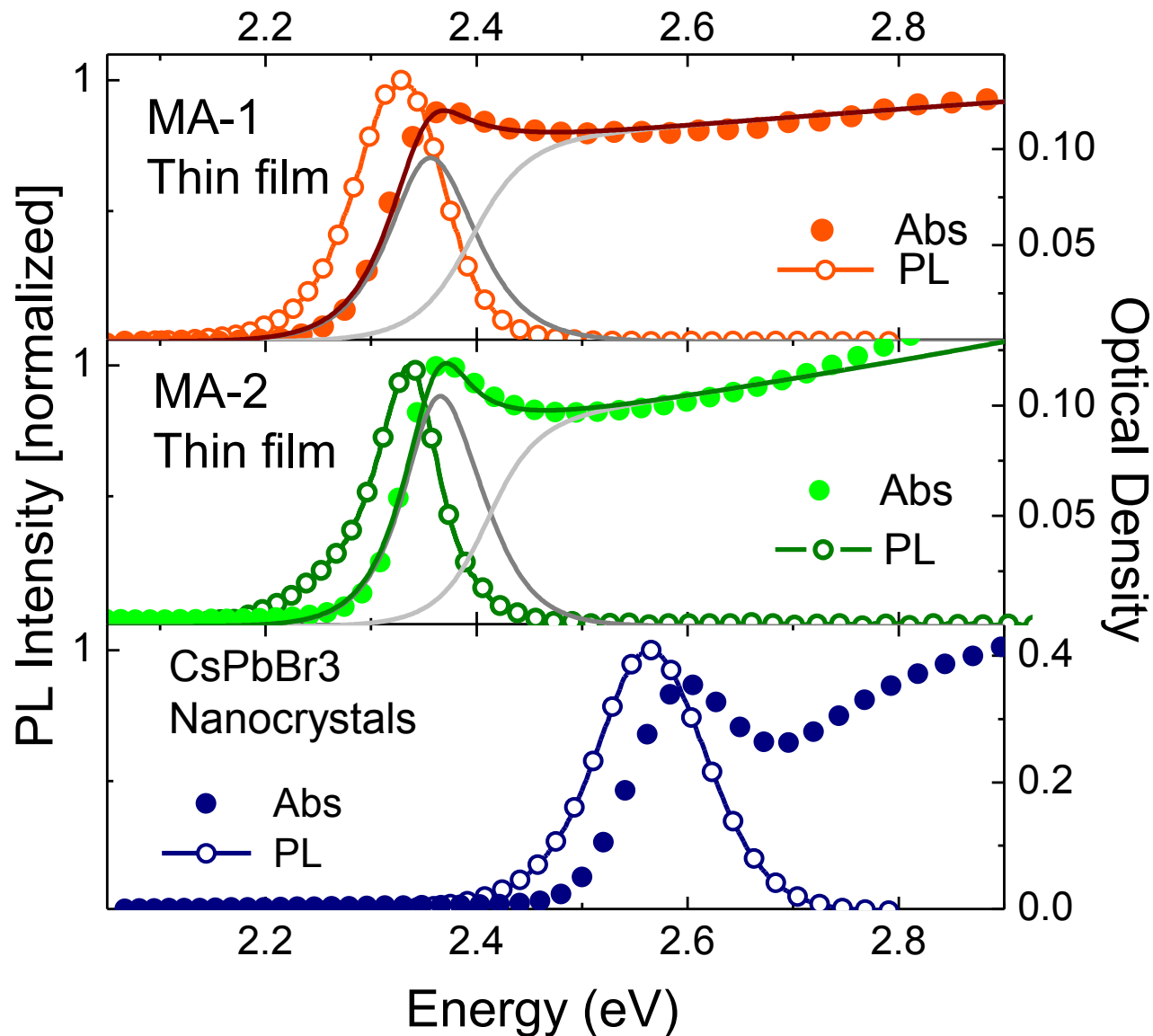
Rosen, Appl. Phys. Lett, 39, 935 (1981).

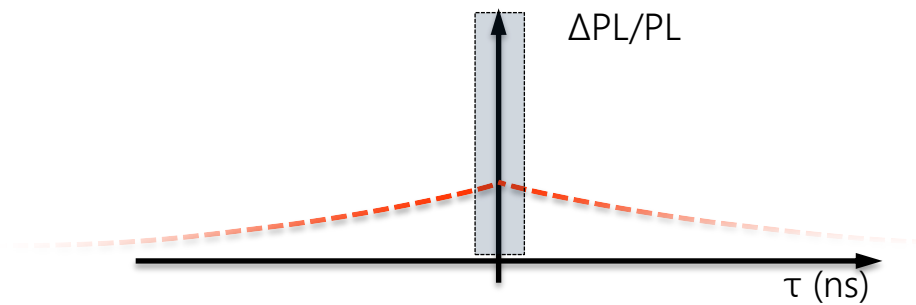
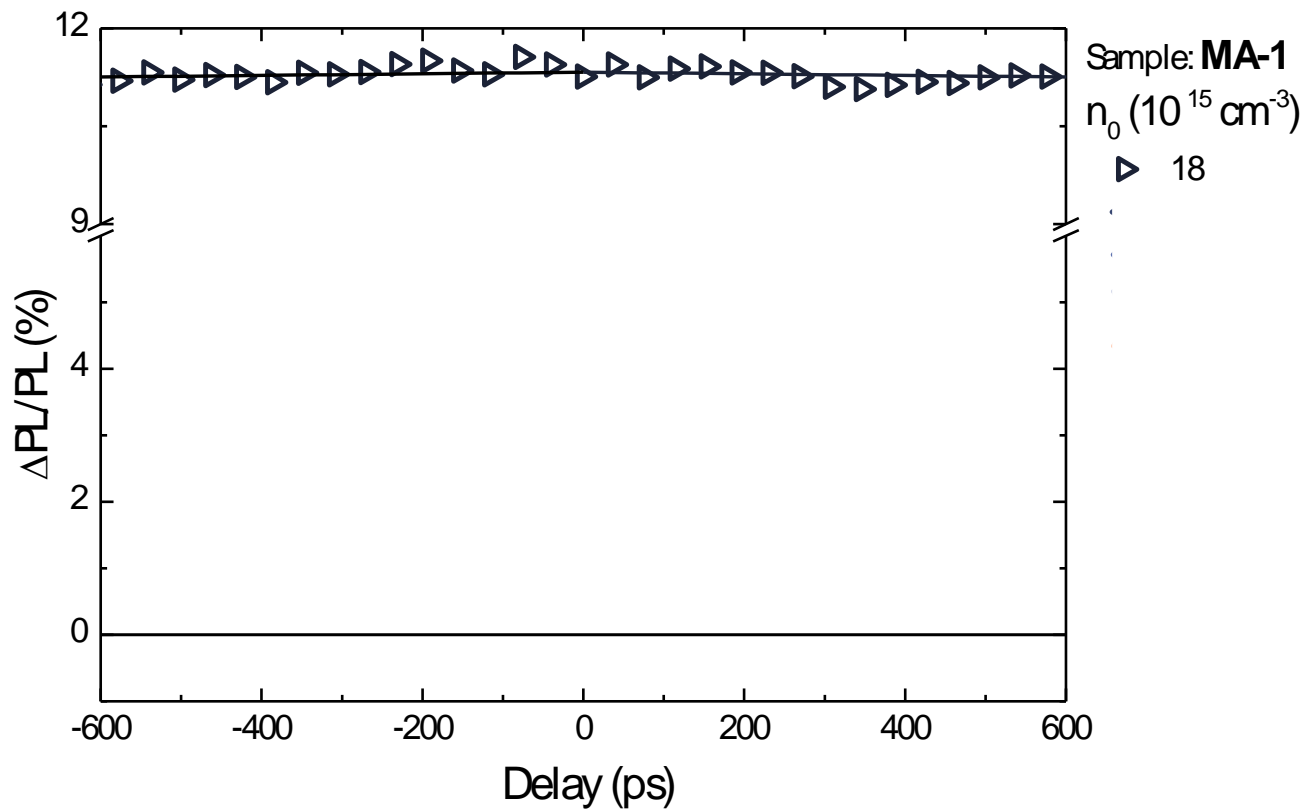
Borgwardt et al, J. Appl. Phys. 117, 215702(2015)

Kandada *et al.* JACS in press

	Rate equation	Steady-state PL TIME INTEGRATED	$\frac{ECPL(\tau = 0, I)}{PL(2I) - 2PL(I)}$ $PL(2I)$
Radiative recombination	$\frac{dn}{dt} = G - Bn^2$	$\propto I$	0
Trap-limited recombination	$\frac{dn}{dt} = G - \gamma_t N_t n - Bnp$	$\propto I^{3/2}$	> 0 $\approx 30\%$
Auger recombination	$\frac{dn}{dt} = G - Bn^2 - \gamma_{auger} n^3$	$\propto I^{2/3}$	< 0

- MA-1 MAPbBr₃: with equal molar precursors
PLQY of < 1%
- MA-2 MAPbBr₃: with excess MABr (1:1.05)
PLQY > 4%
- CsPbBr₃ NX nanocrystals (7.5 nm)

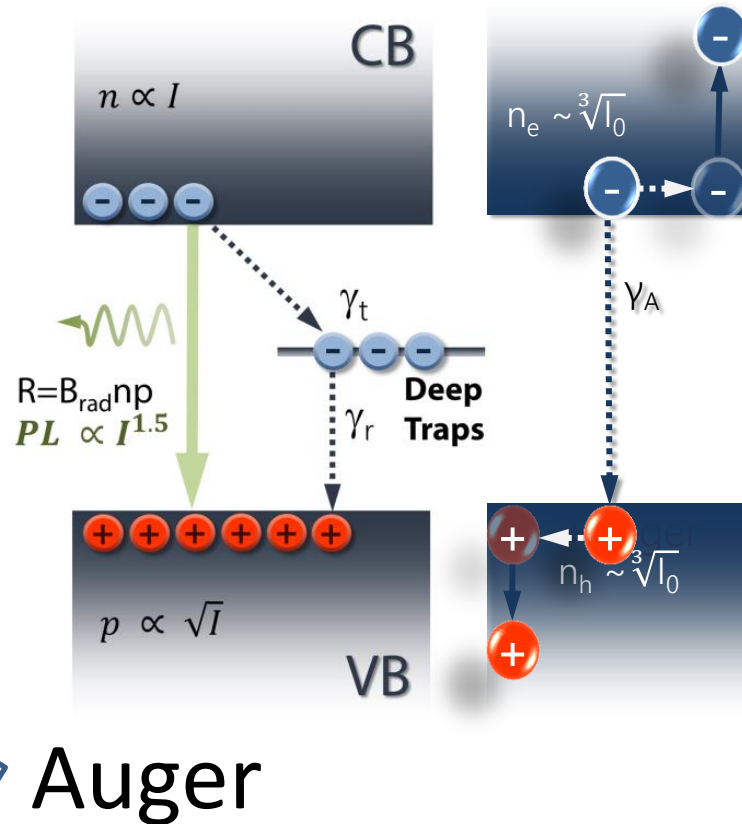
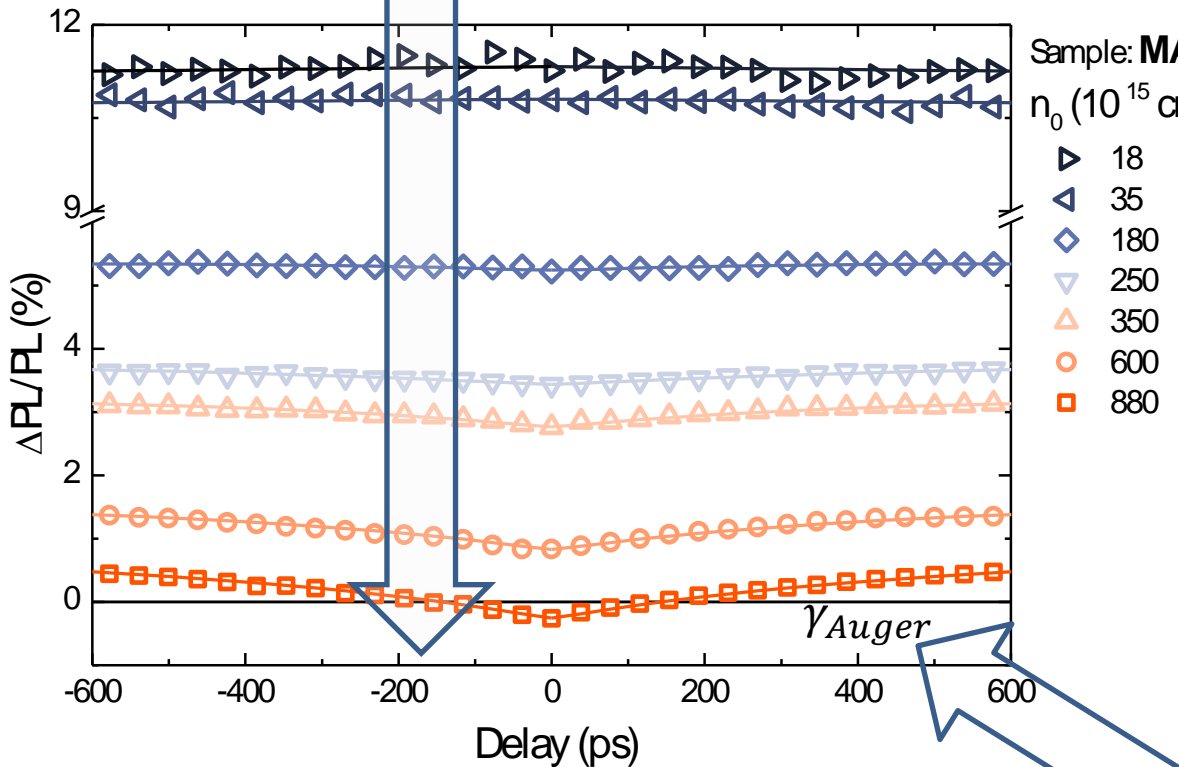




Trap limited (SRH) electron-hole recombination

ECPL: MA-1

Trap filling



$$N_T = 1 \times 10^{17} \text{ cm}^{-3}; B_{rad} = 2 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1};$$

$$\gamma_{Auger} = 1 \times 10^{-27} \text{ cm}^6 \text{ s}^{-1}; \gamma_t = 0.84 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1} \quad \gamma_r = 0.19 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1}$$

Rate Equation Model

$$\frac{dn}{dt} = G - R - \gamma_t(N_t - n_t)n + \gamma_d n_t - \gamma_{Auger} n^2 p$$

$$\frac{dp}{dt} = G - R - \gamma_r n_t p - \gamma_{Auger} n^2 p$$

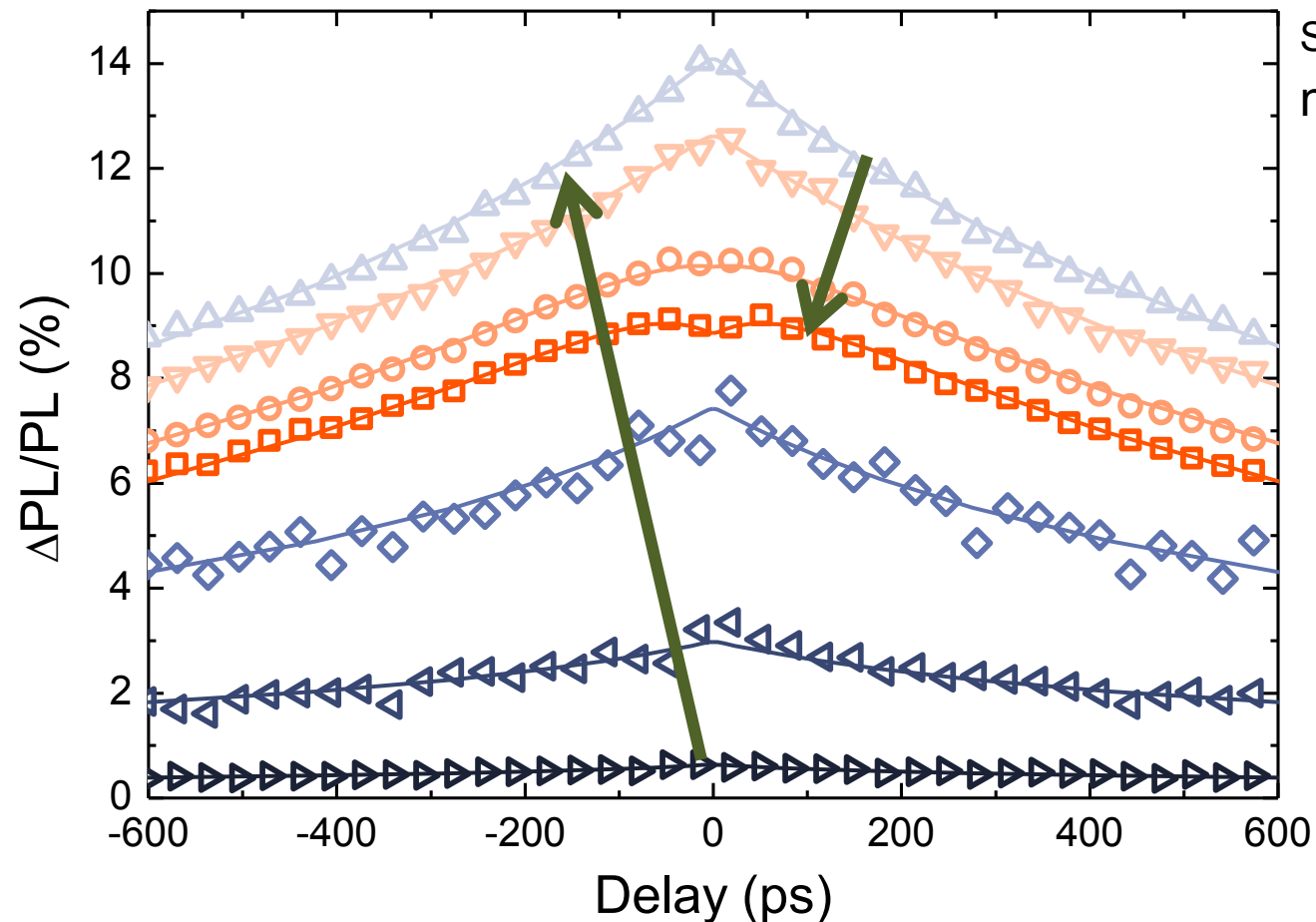
$$\frac{dn_t}{dt} = \gamma_t(N_t - n_t)n - \gamma_r n_t p - \gamma_d n_t$$

$$N_t = 1 \times 10^{17} \text{ cm}^{-3}; \quad B_{rad} = 2 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1};$$

$$\gamma_{Auger} = 1 \times 10^{-27} \text{ cm}^6 \text{ s}^{-1}; \quad \gamma_t = 0.84 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1}$$

$$\gamma_r = 0.19 \times 10^{-9} \text{ cm}^3 \text{ s}^{-1}$$

ECPL: MA-2 Vs MA-1



ECPL reminder:

Traps:

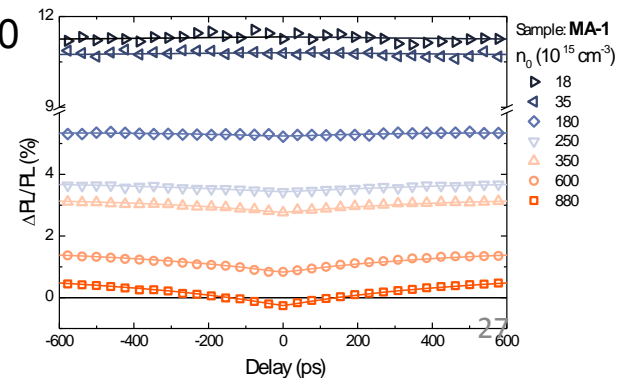
$$PL_{bi} \propto \sqrt[2]{I^3} \quad ECPL > 0$$

Pure radiative:

$$PL_{bi,mono} \propto I_0, \quad ECPL = 0$$

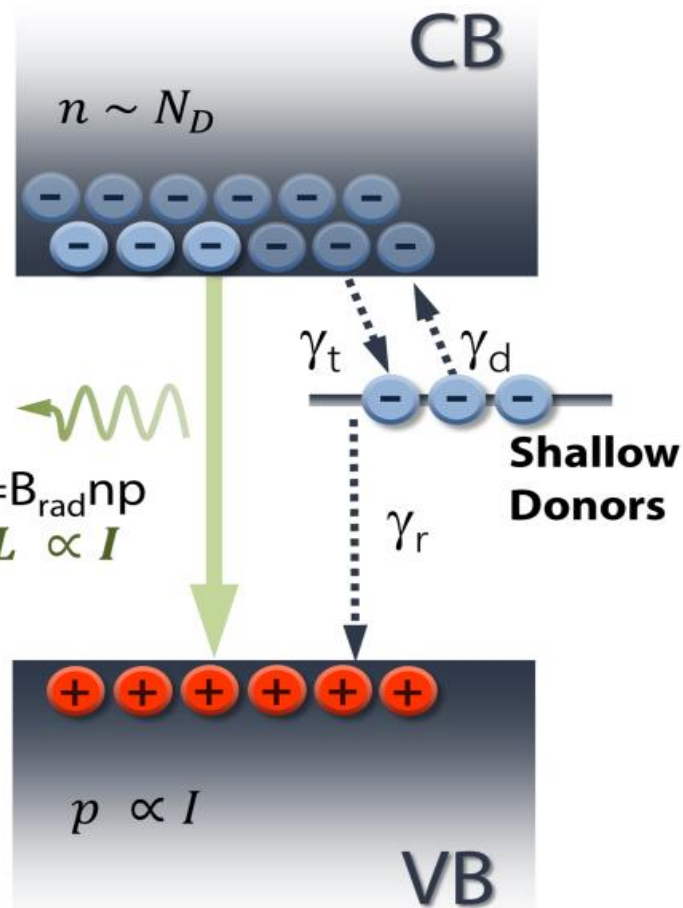
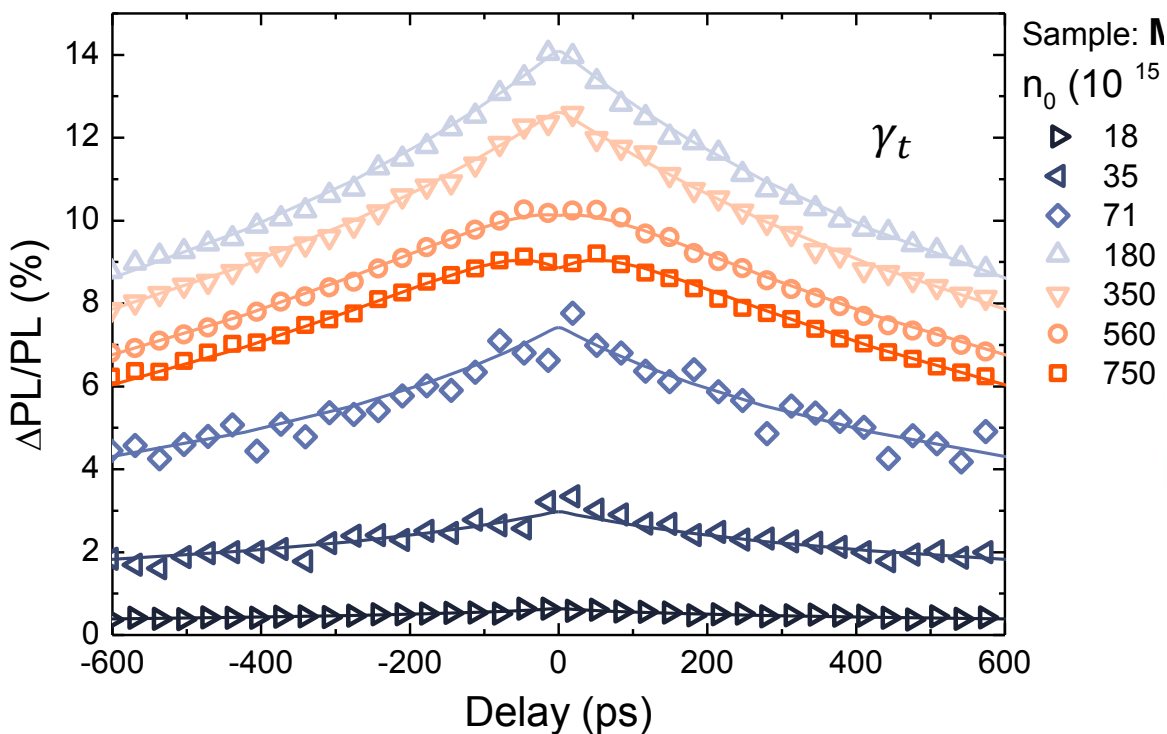
Auger:

$$PL_{bi} \propto \sqrt[3]{I^2}, \quad ECPL < 0$$



ECPL: MA-2

Shallow defects doping



ECPL reminder:

Traps:

$$PL_{bi} \propto \sqrt[2]{I^3} \quad ECPL > 0$$

Pure radiative:

$$PL_{bi,mono} \propto I_0 \quad ECPL = 0$$

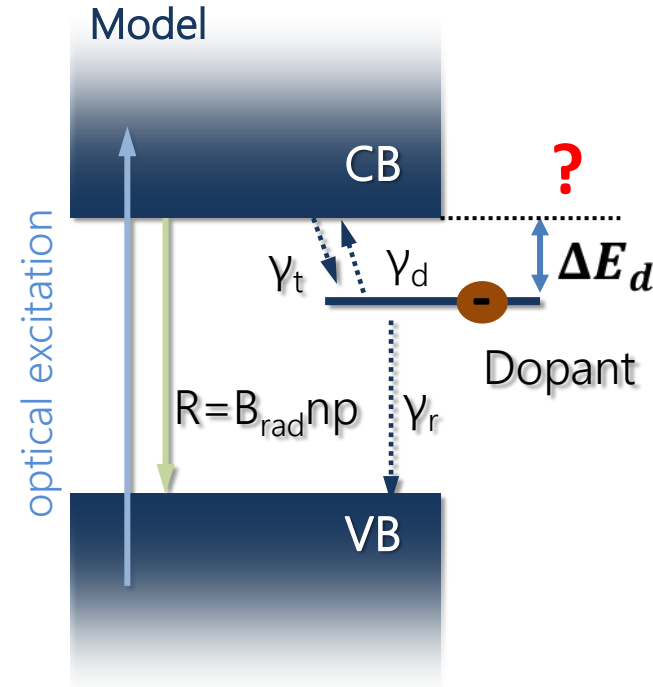
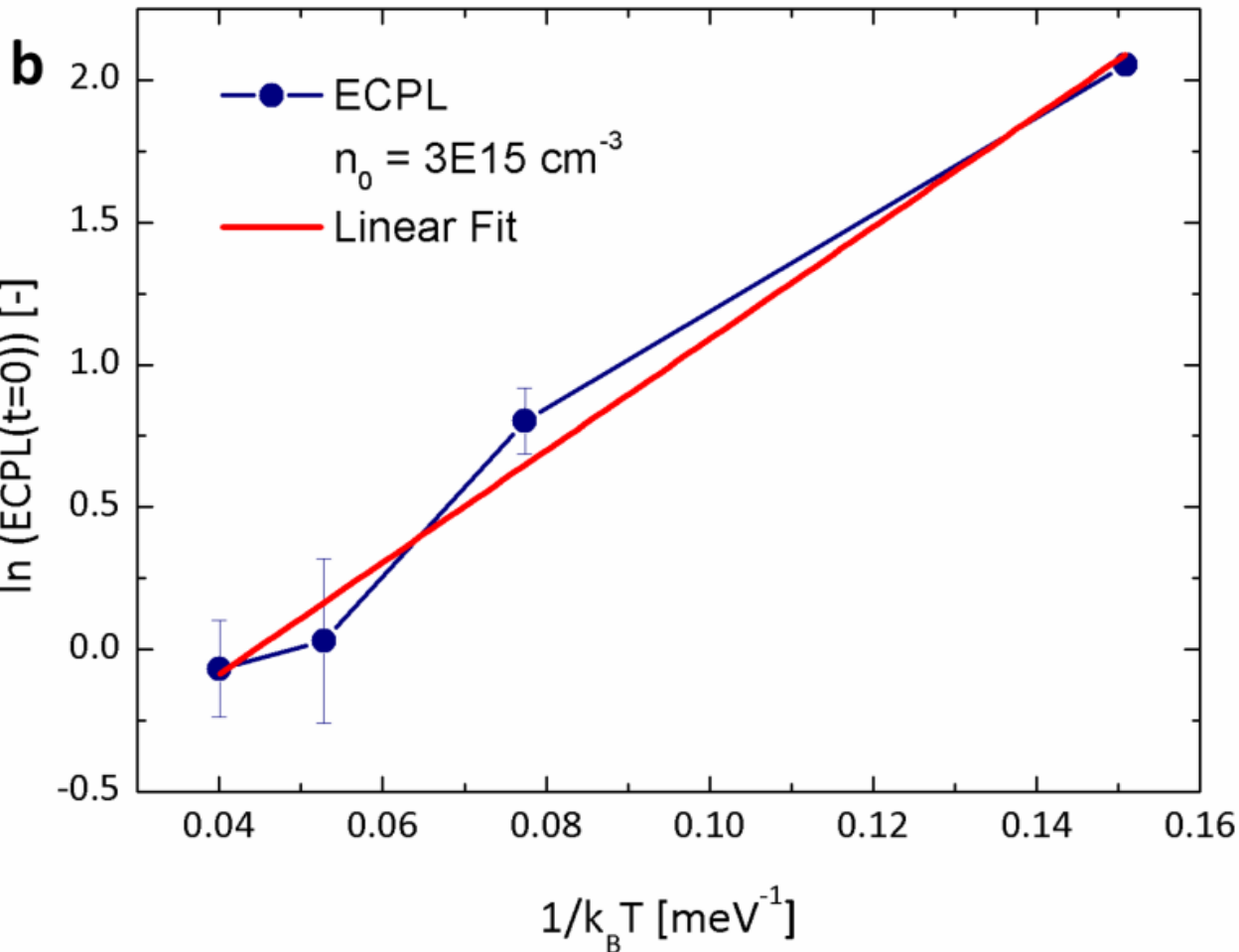
Auger:

$$PL_{bi} \propto \sqrt[3]{I^2}, \quad ECPL < 0$$

$$N_T = 2 \times 10^{18} \text{ cm}^{-3}$$

$$\gamma_t = 3 \times 10^{-8} \text{ cm}^3 \text{ s}^{-1}$$

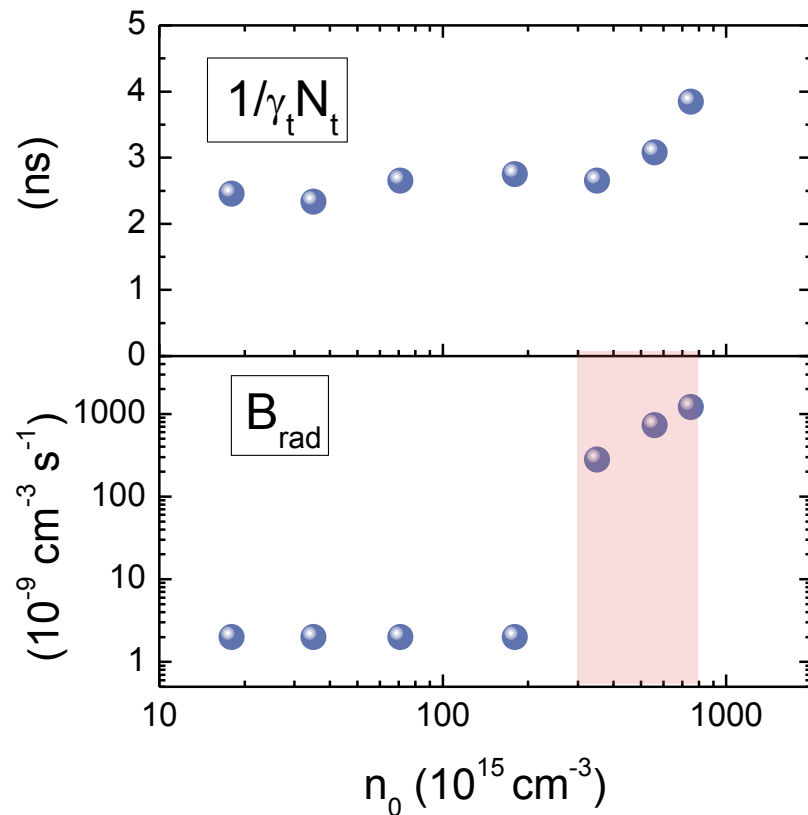
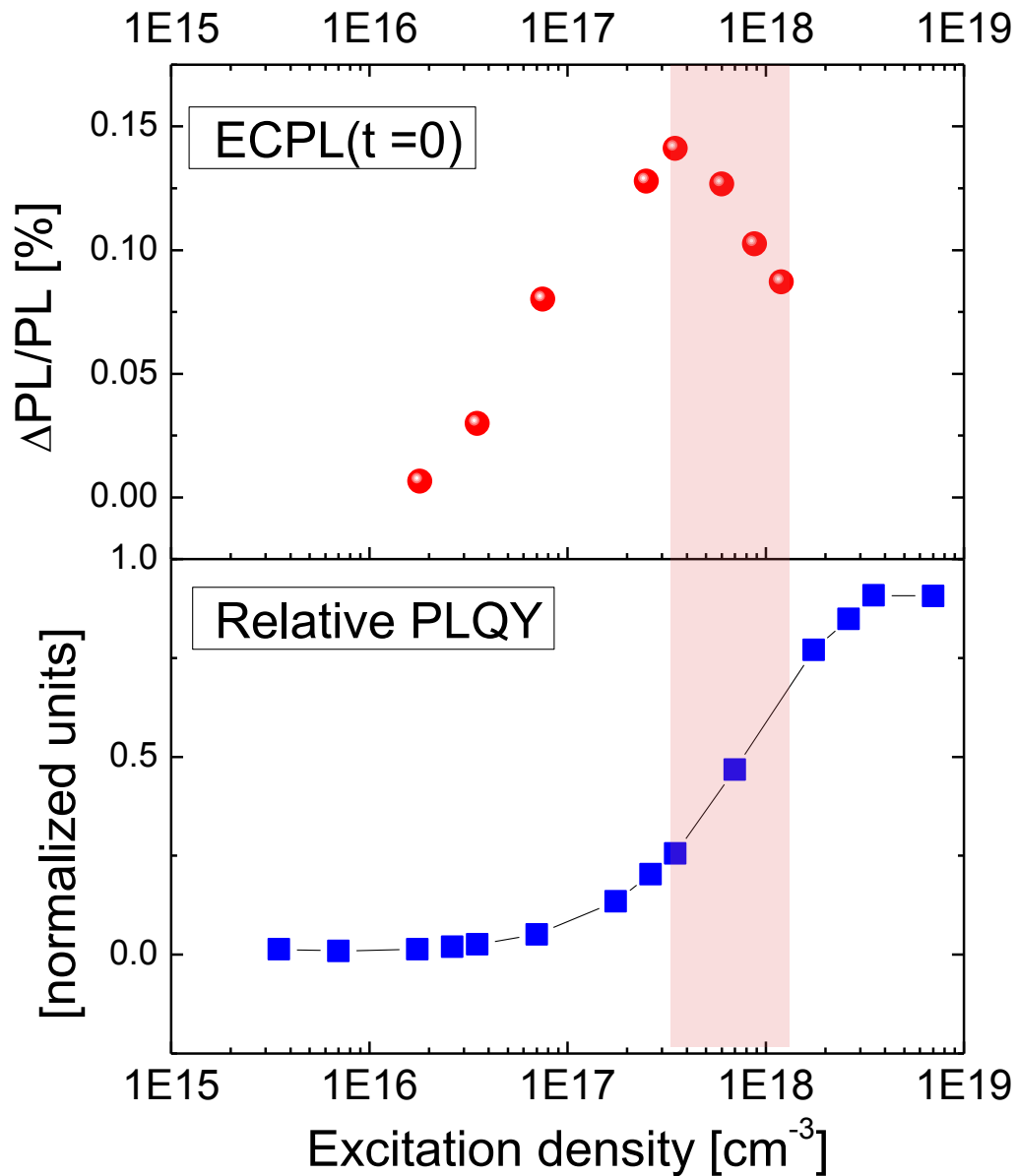
Energetics of the Dopant? Temperature dependence of ECPL



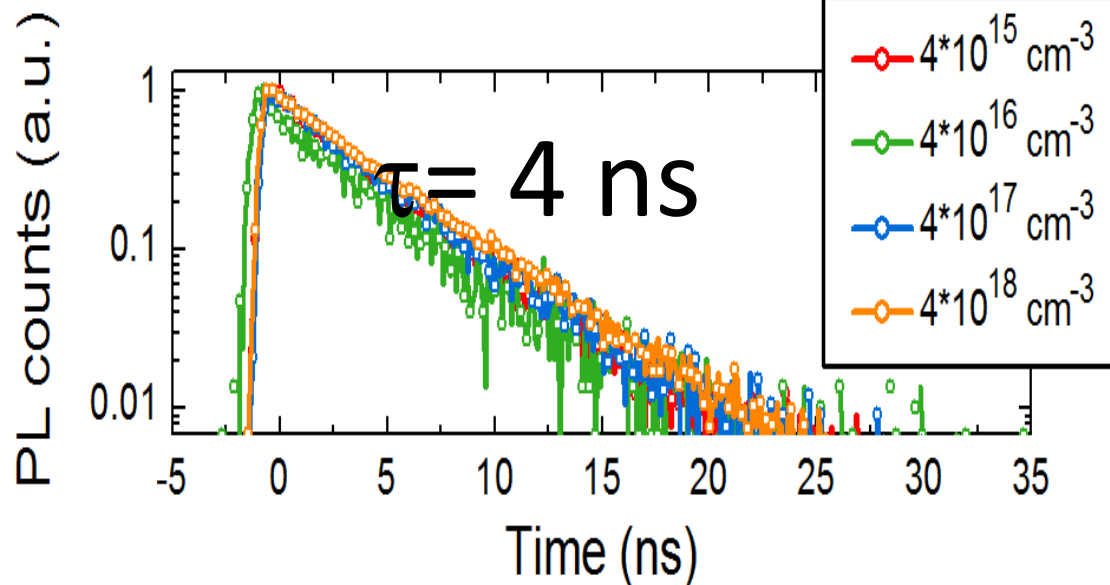
$$N_D \propto \exp\left(-\frac{\Delta E_D}{kT}\right)$$

$$N_D(77K) \sim 0.1 N_D(290K)$$

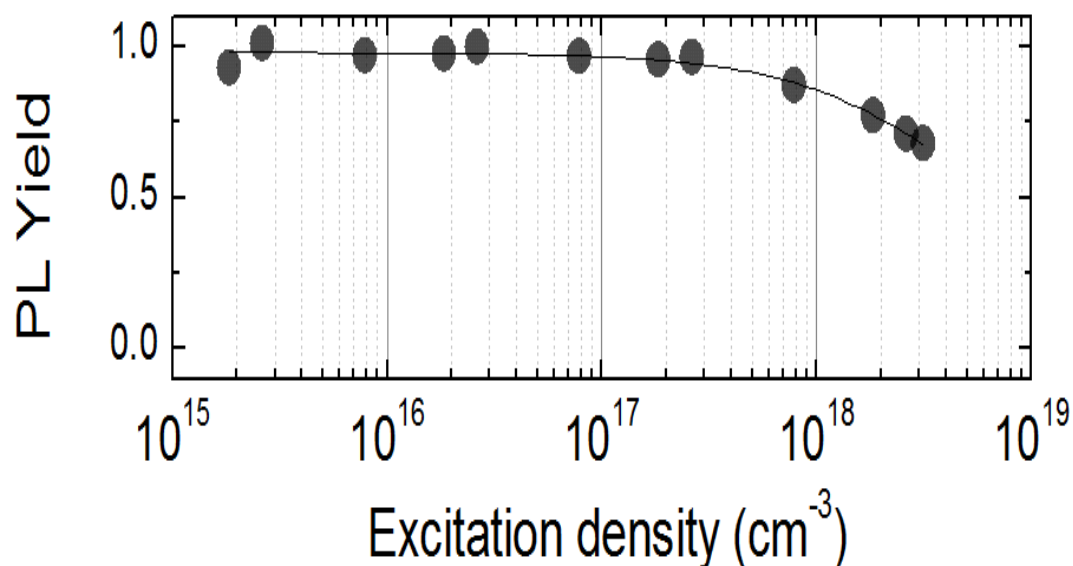
$\rightarrow \Delta E_d \sim 20 \text{ meV}$



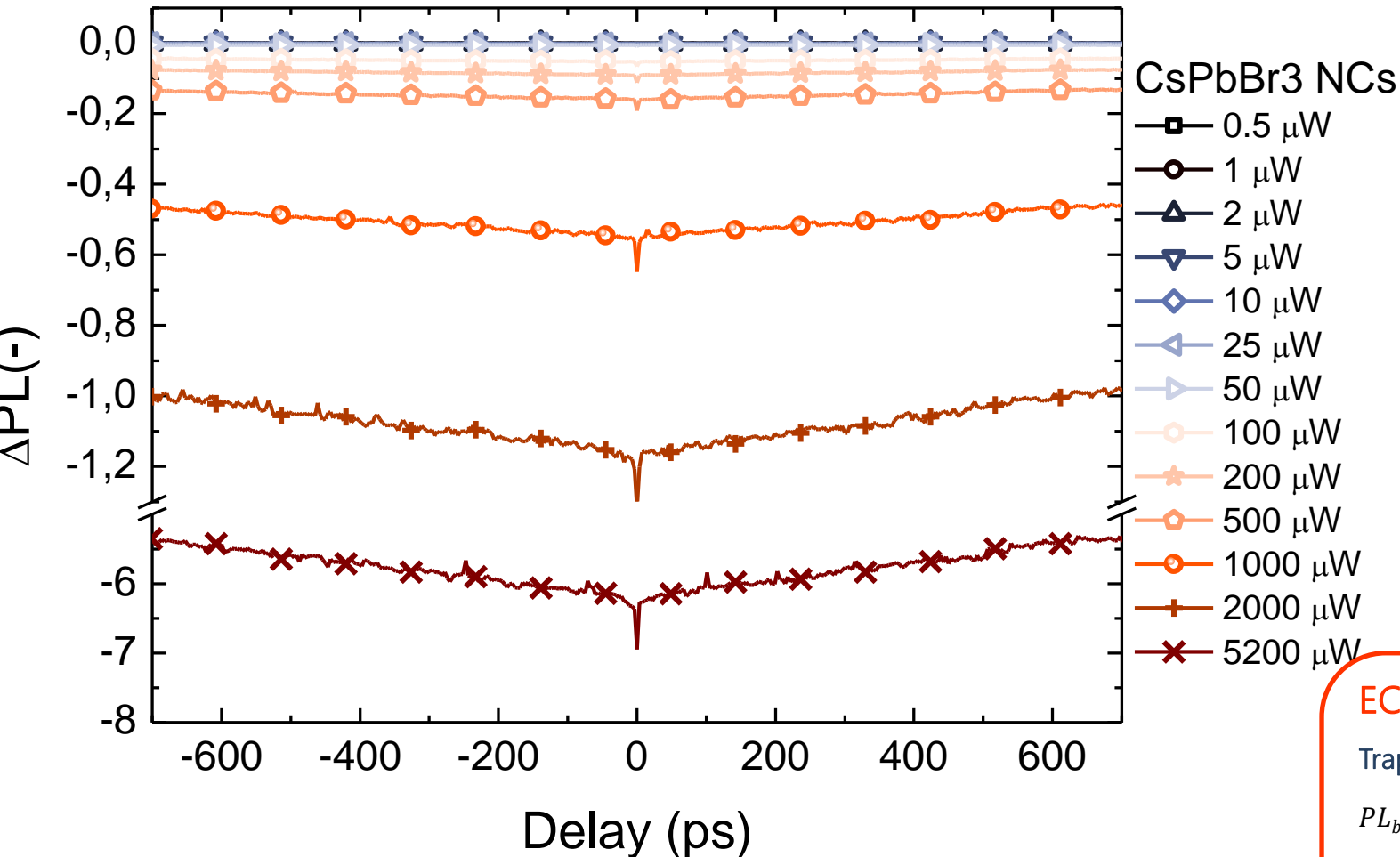
Correlated Regime



$$\frac{dn}{dt} = -\frac{n}{\tau} - k_{nr}n$$



- No trap limited recombination
- **Exciton emission**



Sub-ps Auger Recombination
 Sub ns Exciton Lifetime

ECPL reminder:

Traps:

$$PL_{bi} \propto \sqrt{I^3} \quad ECPL > 0$$

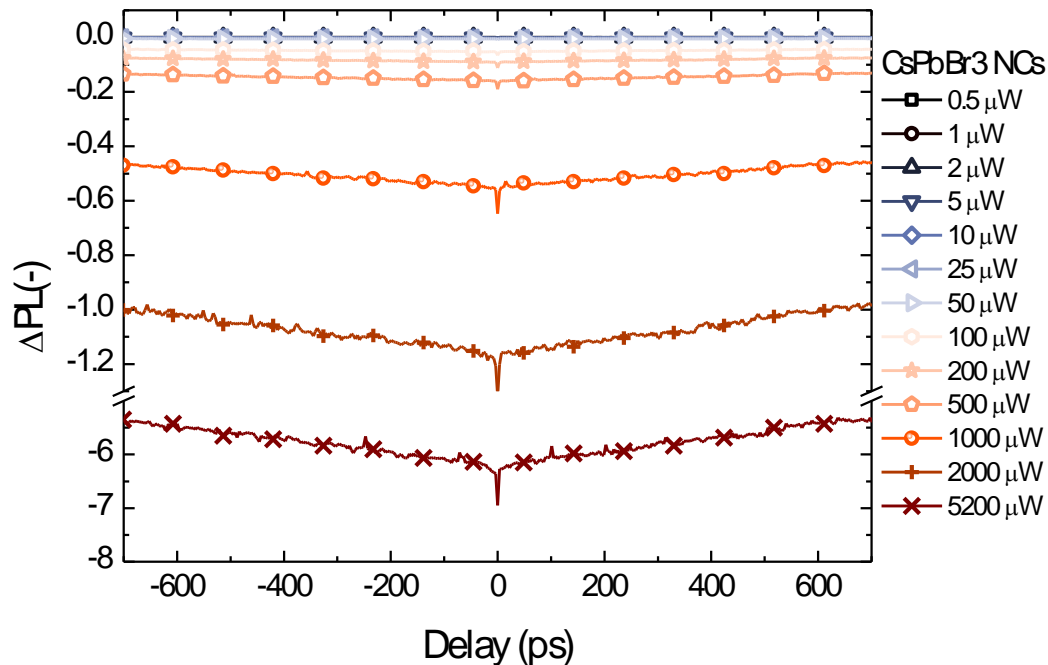
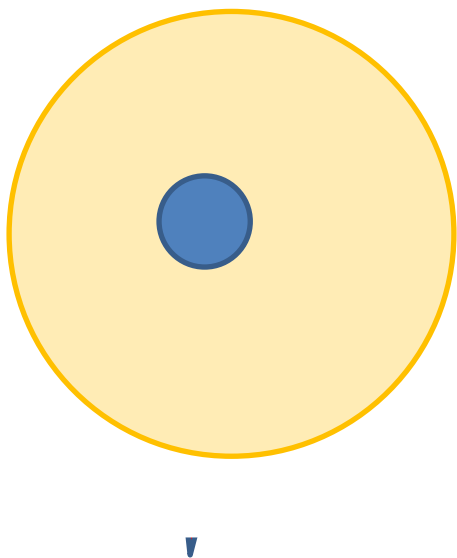
Pure radiative:

$$PL_{bi,mono} \propto I_0, \quad ECPL = 0$$

Auger:

$$PL_{bi} \propto \sqrt[3]{I^2}, \quad ECPL < 0$$

Auger Recombination in sub-ps timescales



Assuming Poissonian distribution

$$PLQY = \frac{1 - e^{-\langle N \rangle}}{\langle N \rangle}$$

$$ECPL = (1 - e^{-2\langle N \rangle}) - 2(1 - e^{-\langle N \rangle})$$

Advanced Materials for Optoelectronics (AOM) Group



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